S2AF THRU S2MF-HAF

SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER Reverse Voltage – 50 to 1000 V

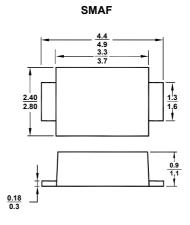
Forward Current – 2 A

Features

- Glass Passivated Chip Juntion
- For surface mount applications
- Low profile package
- · Easy pick and place

Mechanical Data

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, method 2026



All Dimensions in mm

Maximum Ratings and Electrical Characteristics

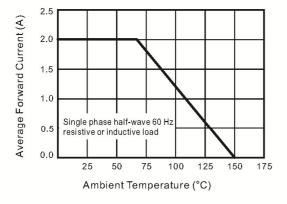
Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbols	S2AF	S2BF	S2DF	S2GF	S2JF	S2KF	S2MF	Units
	Marking	S2A	S2B	S2D	S2G	S2J	S2K	S2M	-
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _a = 65°C	I _{F(AV)}	2							А
Peak Forward Surge Current 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	60							A
Maximum Forward Voltage at 2 A	V _F	1.1							V
Maximum DC Reverse Current $T_a = 25^{\circ}C$ at Rated DC Blocking Voltage $T_a = 125^{\circ}C$	I _R	5 50							μA
Typical Junction Capacitance at $V_R = 4 V$, f = 1 MHz	CJ	30							pF
Typical Thermal Resistance ¹⁾	$R_{ hetaJA}$	50							°C/W
Operating and Storage Temperature Range	T _j , T _{stg}	- 55 to + 150							°C

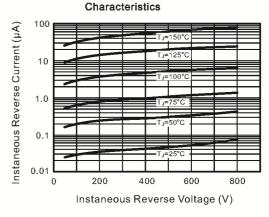
¹⁾ P.C.B. mounted with 0.2 X 0.2" (5 X 5 mm) copper pad areas.



TOP DYNAMIC

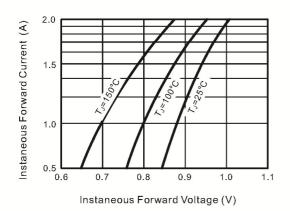


Forward Current Derating Curve

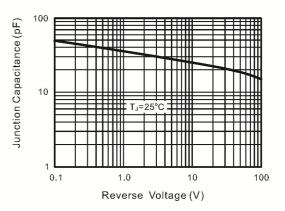


Typical Instaneous Reverse

Typical Forward Characteristic



Typical Junction Capacitance





TOP DYNAMIC